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PCFG60T120SQF

Product Preview IGBT Die

Trench Ultra Field Stop IGBT Die optimized for UPS and Solar applications.

Features

- Extremely Efficient Trench with Field Stop Technology
- Low $V_{CE(sat)}$ Loss Reduces System Power Dissipation
- Optimized for High Speed Switching

Typical Applications

- Solar Inverters
- UPS Systems

MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Collector–Emitter Voltage, $T_J = 25^\circ\text{C}$	V_{CE}	1200	V
DC Collector Current, limited by max $T_{J(max)}$	I_C	(Note 1)	A
Pulsed Collector Current (Note 2)	$I_{C, pulse}$	240	A
Gate–Emitter Voltage	V_{GE}	± 20	V
Operating Junction Temperature	T_J	-55 to $+175$	$^\circ\text{C}$

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Depending on thermal properties of assembly.
2. T_{pulse} limited by T_{Jmax} , 10 μs pulse, $V_{GE} = 15$ V.

MECHANICAL DATA

Parameter	Value	Unit
Die Size	5640 x 5640	μm^2
Emitter Pad Size	See die layout	μm^2
Gate Pad Size	405 x 660	μm^2
Die Thickness	112	μm
Wafer Size	150	mm
Top Pad Metal	5 μm AlCu	
Back Metal	2 μm AlTiNiAg	
Passivation	1.5 μm HR NIT	
Max possible chips per wafer	440	
Reject Ink dot size	25 mils	
Recommended storage environment: In original container, in dry nitrogen, or temperature of 18–28 $^\circ\text{C}$, 30–65% RH	Type: Sawn wafer on tape. Storage time: <3 months	

ORDERING INFORMATION

Device	Inking?	Shipping
PCFG60T120SQF	Yes	Sawn Wafer on Tape

This document contains information on a product under development. ON Semiconductor reserves the right to change or discontinue this product without notice.

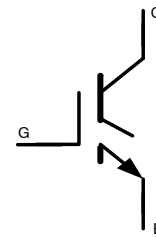


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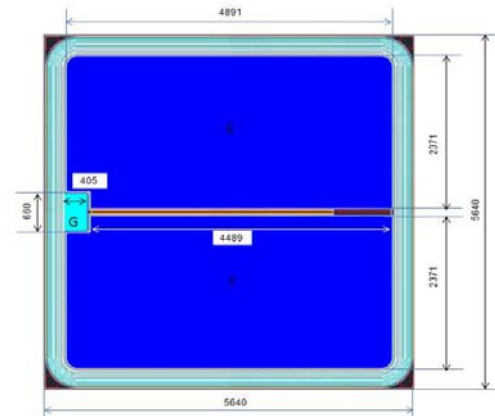
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$V_{CE} = 1200$ V
 $I_C = \text{Limited by } T_{J(max)}$

IGBT DIE



DIE OUTLINE



PCFG60T120SQF

ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$, unless otherwise specified)

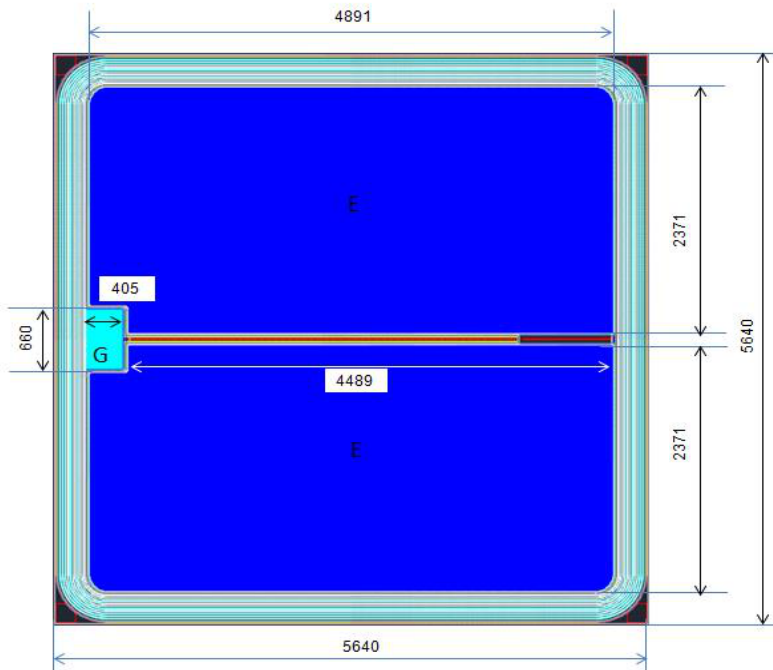
Parameter	Test Conditions	Symbol	Min	Typ	Max	Units
STATIC CHARACTERISTICS						
Collector-Emitter Breakdown Voltage	$V_{GE} = 0\text{ V}, I_C = 500\ \mu\text{A}$	$V_{(BR)CES}$	1200	-	-	V
Collector-Emitter Saturation Voltage	$V_{GE} = 15\text{ V}, I_C = 60\text{ A}, T_J = 25^\circ\text{C}$	$V_{CE(sat)}$	-	1.7	1.95	V
Gate-Emitter Threshold Voltage	$V_{GE} = V_{CE}, I_C = 400\ \mu\text{A}$	$V_{GE(TH)}$	4.5	5.5	6.5	V
Collector-Emitter Cutoff Current	$V_{GE} = 0\text{ V}, V_{CE} = 1200\text{ V}, T_J = 25^\circ\text{C}$	I_{CES}	-	-	400	μA
Gate Leakage Current	$V_{GE} = \pm 20\text{ V}, V_{CE} = 0\text{ V}$	I_{GES}	-	-	± 200	nA

DYNAMIC CHARACTERISTICS

Input Capacitance	$V_{CE} = 20\text{ V}, V_{GE} = 0\text{ V}, f = 1\text{ MHz}$	C_{ies}	-	7280	-	pF
Output Capacitance		C_{oes}	-	198	-	
Reverse Transfer Capacitance		C_{res}	-	113	-	
Gate Charge Total	$V_{CE} = 600\text{ V}, V_{GE} = 15\text{ V}, I_C = 60\text{ A}$	Q_g	-	318	-	nC
Gate-Emitter Charge		Q_{ge}	-	61	-	
Gate-Collector Charge		Q_{gc}	-	153	-	


Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

DIE LAYOUT



E = Emitter Pad
G = Gate Pad
 All dimensions in μm

PCFG60T120SQF

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